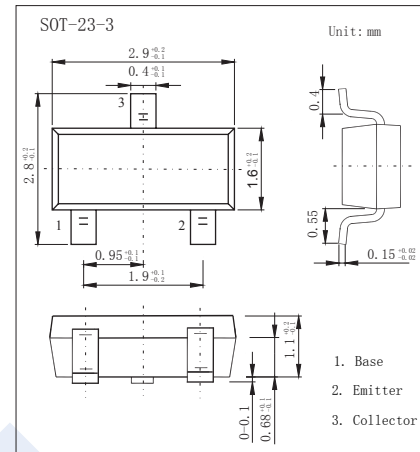


PNP Transistors

2SA1121

■ Features

- Low frequency amplifier
- Complementary pair with 2SC2618



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector to base voltage	V_{CB0}	-35	V
Collector to emitter voltage	V_{CE0}	-35	V
Emitter to base voltage	V_{EB0}	-4	V
Collector current	I_C	-500	mA
Collector power dissipation	P_C	150	mW
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CB0}	$I_C = -100\text{ }\mu\text{A}$, $I_E = 0$	-35			V
Collector- emitter breakdown voltage	V_{CE0}	$I_C = -1\text{ mA}$, $I_B = 0$	-35			
Emitter - base breakdown voltage	V_{EB0}	$I_E = -100\text{ }\mu\text{A}$, $I_C = 0$	-4			
Collector-base cut-off current	I_{CB0}	$V_{CB} = -30\text{ V}$, $I_E = 0$			-0.1	μA
Emitter cut-off current	I_{EB0}	$V_{EB} = -4\text{ V}$, $I_C = 0$			-0.1	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -150\text{ mA}$, $I_B = -15\text{ mA}$		-0.2	-0.6	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -150\text{ mA}$, $I_B = -15\text{ mA}$			-1.2	
Base-emitter voltage	V_{BE}	$I_C = -10\text{ mA}$, $V_{CE} = -3\text{ V}$		-0.64		
DC current transfer ratio	h_{FE}	$I_C = -10\text{ mA}$, $V_{CE} = -3\text{ V}$	100		320	
		$I_C = -500\text{ mA}$, $V_{CE} = -3\text{ V}$	10			

■ $h_{FE}(1)$ Classification

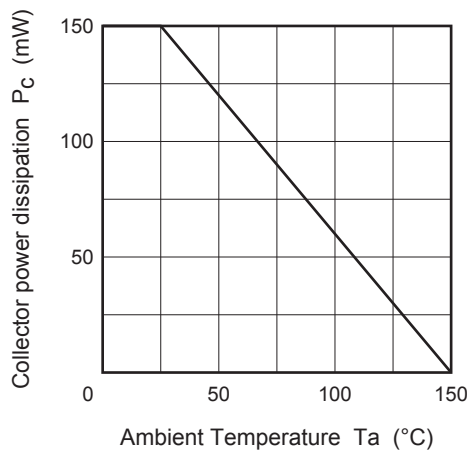
Type	2SA1121-C	2SA1121-D
Range	100-200	160-320
Marking	SC	SD

PNP Transistors

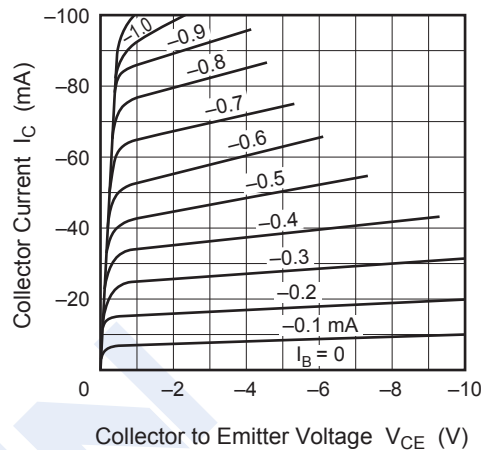
2SA1121

■ Typical Characteristics

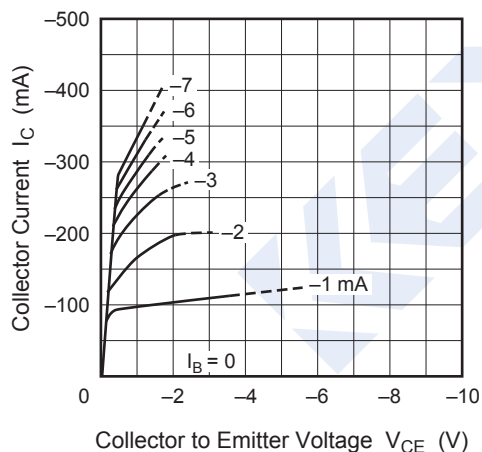
Maximum Collector Dissipation Curve



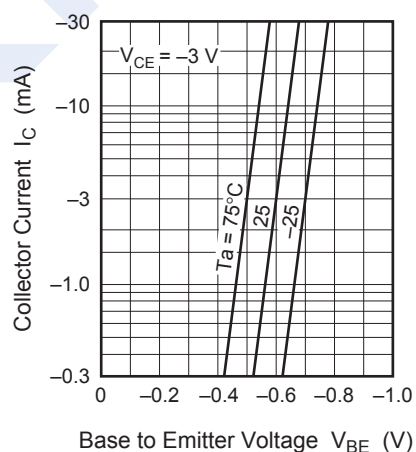
Typical Output Characteristics (1)



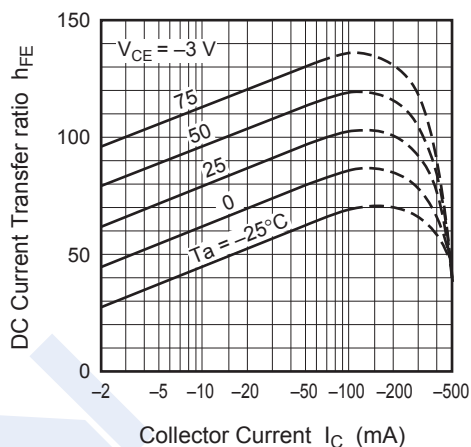
Typical Output Characteristics (2)



Typical Transfer Characteristics



DC Current Transfer Ratio vs. Collector Current



Gain Bandwidth Product vs. Collector Current

